

Figure 1: (a) Schematic of the NIR upconverter components in series, as demonstrated in this work. (b) Circuit diagram of the NIR upconverter where V_D , V_{LED} , and V_{CE} refer to voltage drops across the full device, the LED, and HPT, respectively. (c) Schematic showing future work where the LED will be metalmetal bonded to the HPT with the LED substrate removed.

Figure 2: (a) False color cross-sectional SEM of the HPT and (b) stack diagram of the HPT growth labeling the layer composition, thickness, growth temperature, and nominal bulk doping.

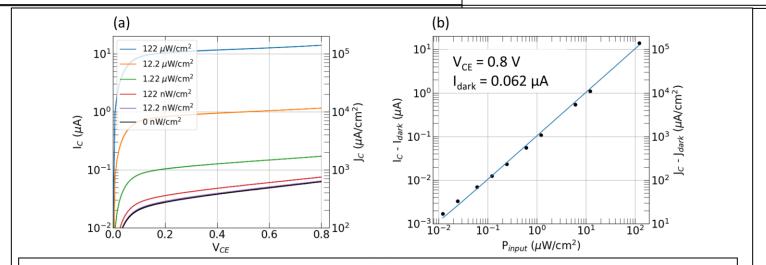
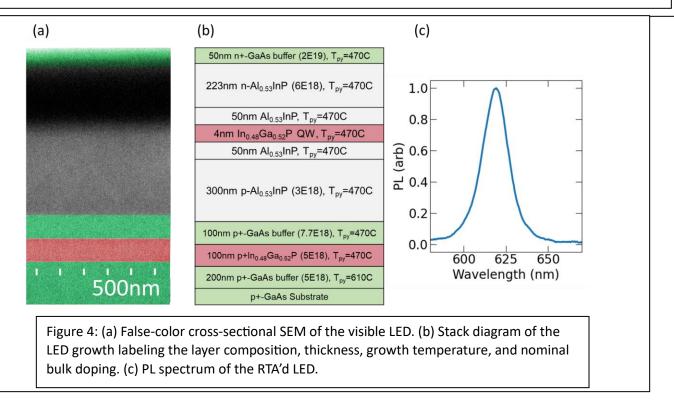
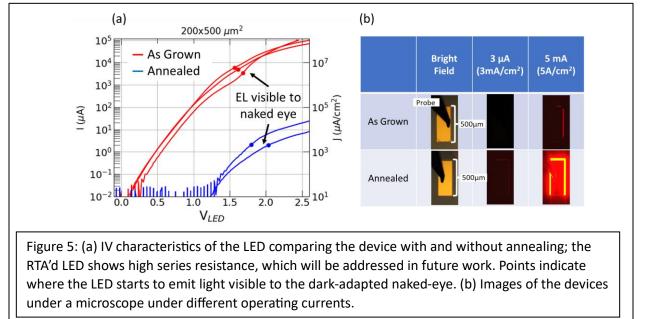
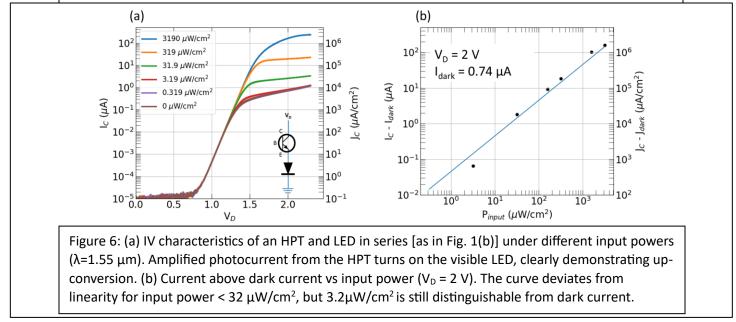


Figure 3: (a) IV characteristics of the HPT under different input powers (λ =1.55 µm). An input power density as low as 12.2 nW/cm² generates a current signal I_C that is distinguishable from the dark current. (b) Current above dark current vs input power (V_{CE} = 0.8V) showing linear response.







Bibliography

1. Spitzer, Cary R., and Cary Spitzer, eds. *Digital Avionics Handbook*. CRC press, (2000): 126-135.